Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2589	(118/500,501).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/04 16:50
L2	703	(semiconductor$1 or wafer$1) and cup same drain$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 16:56
L3	25	1 and 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 16:55
L4	46	(semiconductor$1 or wafer$1) and catch$3 same cup same drain$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 16:55
L6	0	1 and 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 16:56
L7	822	(semiconductor$1 or wafer$1) and cup same (drain$1 or drip$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 16:56
L8	25	1 and 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 16:56
S2	176	(yewebdar or tadesse) and ("118"/$.ccls. or "264"/$.ccls.)	US-PGPUB; USPAT	OR	OFF	2005/02/25 16:07
S77	12	(("6,432,199") or ("5,705,223") or ("5,947,136") or ("5,762,709") or ("6,533,864") or ("5,940,651")).PN. or ((2003/101929) or (2003/183250)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/25 16:07

S78	6	(("6,432,199") or ("5,705,223") or ("5,947,136") or ("5,762,709") or ("6,533,864") or ("5,940,651")).PN. or ((2003/101929) or (2003/183250)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:44
S84	1	("20030101929").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/25 16:12
S85	1	("20030183250").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/25 16:12
S86	8	(("6,432,199") or ("5,705,223") or ("20030101929") or ("5,947,136") or ("5,762,709") or ("6,533,864") or ("5,940,651") or ("20030183250")).PN.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:44
S88	1	S86 and (catch$3 and drain$3 and trap)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:24
S89	0	S86 and de near gas$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 09:48
S90	0	S86 and de-gas$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 09:48
S91	293	(semiconductor$1 or wafer$1) and de near gas$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 10:32
S92	210	(semiconductor$1 or wafer$1) and de-gas$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 09:53
S93	11	(semiconductor$1 or wafer$1) and (de-gas$3 same separat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 09:55

S94	1364	(118/52,612).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/28 09:53
S95	20145	(semiconductor$1 or wafer$1) and (separat$3 near5 (gas or fluid or liquid))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 09:56
S96	27	(semiconductor$1 or wafer$1) and (separat$3 near5 (gas or fluid or liquid)) same liquid near trap	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 10:31
S97	25	S96 and vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 10:02
S98	27	(semiconductor$1 or wafer$1) and (catch near cup) same drain$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:24
S99	2	S98 and frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:38
S100	1	(semiconductor$1 or wafer$1) and (catch near cup) same frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:05
S101	1	(semiconductor$1 or wafer$1) and (catch near cup) same (frame or casing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:06
S102	1253	(semiconductor$1 or wafer$1) and (cup) same (frame or casing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:07

S10 3	533	(semiconductor$1 or wafer$1) and (cup) near7 (frame or casing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:07
S10 4	348	(semiconductor$1 or wafer$1) and (cup) near3 (frame or casing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:07
S10 5	293	(semiconductor$1 or wafer$1) and (cup) near7 (frame)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:08
S10 7	15	(semiconductor$1 or wafer$1) and (cup) near7 (frame) and drain$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:08
S10 8	14	S98 and lip	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 16:49
S10 9	0	S86 and solvent near bath	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:24
S11 0	30	(semiconductor$1 or wafer$1) and (solvent near bath) same drain$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 16:50
S11 1	5	S110 and frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:39

S112	22	S110 and (evaporat$3 or saturat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:55
S113	5	(semiconductor$1 or wafer$1) and (solvent near bath) same drain$1 same (evaporat$3 or saturat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 12:00
S114	31	(semiconductor$1 or wafer$1) and (solvent near bath) same (evaporat$3 or saturat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 12:02
S115	11	(semiconductor$1 or wafer$1) and (solvent near bath) near5 (evaporat$3 or saturat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 11:10
S116	1037	(430/327).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/02 16:50
S117	51	nguyen-andrew$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 16:50
S118	1433	(427/240).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/03 10:39
S119	2	jp-2002151376$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 10:40
S120	2	("20020053319").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/03 10:44

S12 1	11	(semiconductor$1 or wafer$1) and (solvent near bath) near5 (evaporat$3 or saturat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 15:21
S12 2	124	(semiconductor$1 or wafer$1) and (wash$3 or clean$3)near5 (head$1 or nozzle$1)same (evaporat$3 or saturat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 15:23
S12 3	13	(semiconductor$1 or wafer$1) and (wash$3 or clean$3)near5 (head$1 or nozzle$1)near7 (evaporat$3 or saturat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 09:24
S12 4	807	(118/302).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/04 09:24
S12 5	643	(118/319).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/04 09:26
S12 6	628	(239/104,106).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/04 09:26
S12 7	6	(semiconductor$1 or wafer$1) and catch$3 near5 cup same lip	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 16:50